

Supporting Information

High responsivity and low dark current nonpolar GaN-based ultraviolet photo-detectors

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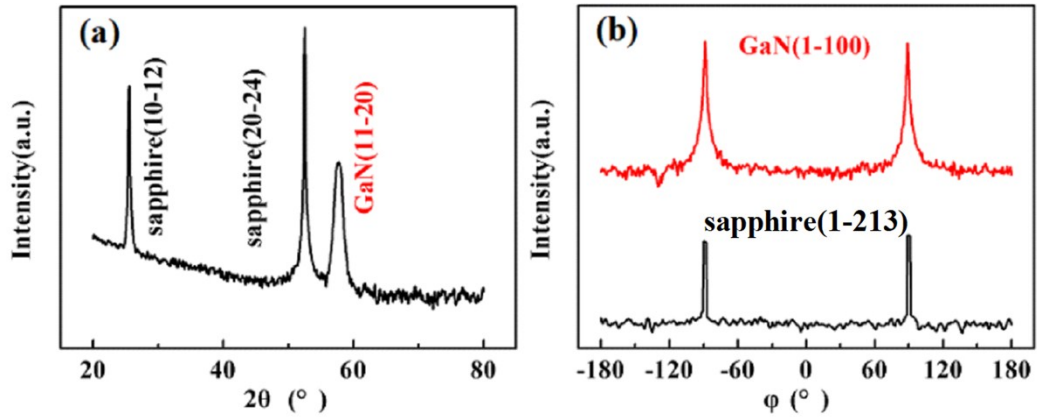


Figure S1. (a) XRD 2θ - ω and (b) ϕ scans for *a*-plane GaN epitaxial films grown on *r*-plane sapphire substrates

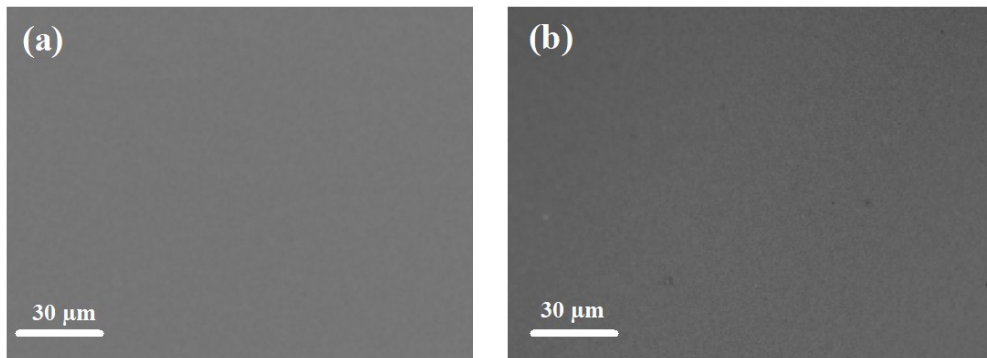


Figure S2. Optical microscopy image for nonpolar GaN epitaxial films of (a) sample 1 and (b) sample 2

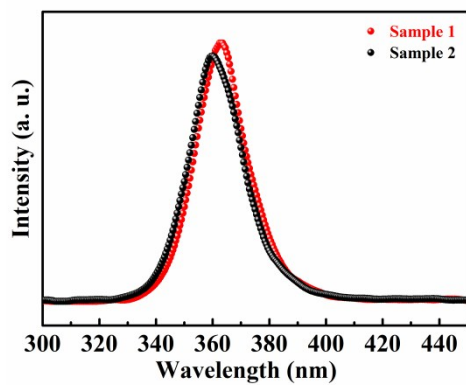


Figure S3. Photoluminescence spectra for nonpolar GaN epitaxial films in sample 1 and sample 2